



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

P-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 20 Volts CURRENT 3.5 Ampere

CHM3413KGP

Halogens free devices

APPLICATION

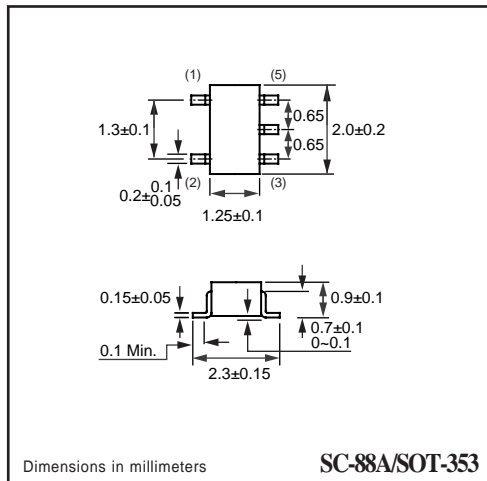
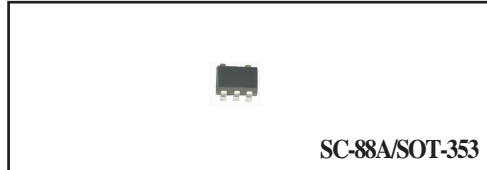
- * Servo motor control.
- * Power MOSFET gate drivers.
- * Other switching applications.

FEATURE

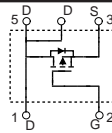
- * Small flat package. (SC-88A)
- * High density cell design for extremely low Rds(ON).
- * Rugged and reliable.
- * High saturation current capability.

CONSTRUCTION

- * P-Channel Enhancement



CIRCUIT



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	CHM3413KGP	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Maximum Drain Current - Continuous	-3.5	A
	- Pulsed	-15	
P_D	Maximum Power Dissipation	625	mW
T_J	Operating Temperature Range	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	250	$^\circ\text{C/W}$
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ELECTRICAL CHARACTERISTIC (CHM3413KGP)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSSF}	Gate-Body Leakage	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			+100	nA
I_{GSSR}	Gate-Body Leakage	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

ON CHARACTERISTICS (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.36		-0.8	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -3.4\text{ A}$		76	95	m Ω
		$V_{GS} = -2.5\text{ V}, I_D = -2.4\text{ A}$		97	120	
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -2.8\text{ A}$		6		S

SWITCHING CHARACTERISTICS (Note 4)

Q_g	Total Gate Charge	$V_{DS} = -6\text{ V}, I_D = -2.8\text{ A}$ $V_{GS} = -4.5\text{ V}$		4.8	8	nC
Q_{gs}	Gate-Source Charge			1		
Q_{gd}	Gate-Drain Charge			1		
t_{on}	Turn-On Time	$V_{DD} = -6\text{ V}$ $I_D = -1.0\text{ A}, V_{GEN} = -4.5\text{ V}$ $R_G = 6\ \Omega$		10	16	nS
t_r	Rise Time			13	23	
t_{off}	Turn-Off Time			18	25	
t_f	Fall Time			15	20	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I_S	Drain-Source Diode Forward Current				-1.5	A
V_{SD}	Drain-Source Diode Forward Voltage	$I_S = -1.5\text{ A}, V_{GS} = 0\text{ V}$			-1.2	V